Nano Current Power IoSmart™ Switch with True Reverse Current Blocking

Product Specification

DESCRIPTION

The GLF1201Q is an advanced technology fully integrated I_QSmart[™] load switch device with True Reverse Current Blocking (TRCB) technology and the slew rate control of the output voltage. The best in class efficiency makes it an ideal choice for electronics requiring operation under the high temperature up to 125 °C.

The GLF1201Q offers an industry leading True Reverse Current Blocking (TRCB) performance, featuring an ultra-low threshold voltage. It minimizes reverse current flow in an event that the VOUT pin voltage exceeds the VIN voltage.

An integrated slew rate control can also enhance system reliability by mitigating bus voltage swings during switching events. Where uncontrolled switches can generate high inrush currents that result in voltage droop and/or bus reset events, the GLF slew rate control specifically limits inrush currents during turn-on to minimize voltage droop.

The GLF1201Q load switch device supports an industry leading wide input voltage range and helps to improve operating life and system robustness. Furthermore, one device can be used in multiple voltage rail applications which helps to simplify inventory management and reduces operating cost.

FEATURES

- AEC-Q100 Qualified
- Qualified for Automotive Applications:
 Temperature Grade 1: Ambient Operating
 Temperature Range: 40 °C ~ +125 °C
- Wide Input Range: 1.5 V to 5.5 V

6 V abs max

- True Reverse Current Blocking
- R_{ON}: $60 \text{ m}\Omega$ Typ at 5.5 V_{IN}

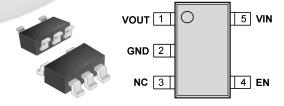
• I_{OUT} Max: 2 A

- Ultra-Low I_Q: 0.48 μA Typ at 5.5 V_{IN}
- Ultra-Low I_{SD}: 25 nA Typ at 5.5 V_{IN}
- Controlled Rise Time: 600 μs at 3.3V_{IN}
- Internal EN Pull-Down Resistor on
- Integrated Output Discharge Switch
- ESD Performance Tested per AEC Q100 HBM: 4 kV, CDM: 2 kV
- Moisture Sensitivity Level: MSL-3 and 260 °C
 Peak Reflow Temp
- Lead-free, Halogen-free, and Adhere to RoHS Directive

APPLICATIONS

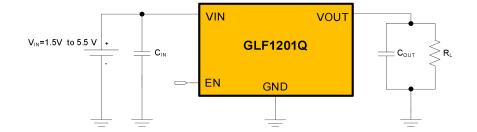
- Automotive Electronics
- Infotainment Systems
- · Diagnosis System

PACKAGE



SOT23-5L

APPLICATION DIAGRAM



ALTERNATE DEVICE OPTIONS

| Part Number | Top Mark | R _{on} (Typ) at 5.5 V _{IN} | TRCB | Output Discharge | EN Activity |
|---------------|----------|---|------|---------------------|----------------|
| GLF1201Q-T1G7 | DN | 60 mΩ | Yes | 85 Ω | High |

FUNCTIONAL BLOCK DIAGRAM

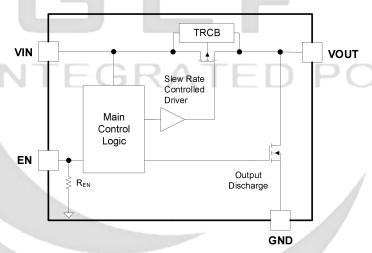


Figure 1. Functional Block Diagram

PIN CONFIGURATION

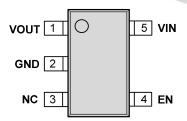


Figure 2. SOT23-5L

PIN DEFINITION

| Pin# | Name | Description |
|------|------|-------------------------------------|
| 1 | VOUT | Switch Output |
| 2 | GND | Ground |
| 3 | NC | No connection |
| 4 | EN | Enable to control the switch |
| 5 | VIN | Switch Input. Supply Voltage for IC |



ABSOLUTE MAXIMUM RATINGS

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions; extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

| Symbol | | Min. | Max. | Unit | |
|------------------|---|---|------|------|----|
| Vin | V _{IN} , V _{OUT} , V _{EN} to GND | V _{IN} , V _{OUT} , V _{EN} to GND | | | |
| l _{out} | Maximum Continuous Switch Curre | Maximum Continuous Switch Current | | | |
| T _{STG} | Storage Junction Temperature | -65 | 150 | °C | |
| TJ | Operating Temperature Range | | 150 | °C | |
| θ _{JC} | Thermal Resistance, Junction to Ca | | 90 | °C/W | |
| θЈА | Thermal Resistance, Junction to Ar | | 180 | °C/W | |
| ECD | Flactrostatic Discharge Conchility | Human Body Model, per AEC Q100-002 | 4 | | kV |
| ESD | Electrostatic Discharge Capability | Charged Device Model, per AEC Q100-011 | 2 | | ĸV |

Note. The θ_{JA} is measured at $T_A = 25^{\circ}$ C on a high effective thermal conductivity four-layer test board per JEDEC 51-7.

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min. | Max. | Unit |
|-----------------|-------------------------------|------|------|------|
| V_{IN} | Supply Voltage | 1.5 | 5.5 | ٧ |
| TA | Ambient Operating Temperature | -40 | +125 | °C |

ELECTRICAL CHARACTERISTICS

Values are at V_{IN} = 3.3V and T_A = 25°C unless otherwise noted.

| Symbol | Parameter | Cond | Min. | Тур. | Max. | Units | |
|-----------------|---|---|-------------------------|------|------|-------|-------|
| Basic Ope | eration | | | | | | |
| | Ovince to Commont (1) | V _{IN} = V _{EN} =5.5 V, I _{OUT} =0 m | ıA | | 0.48 | 0.60 | |
| lα | Quiescent Current (1) $V_{\text{IN}} = V_{\text{EN}} = 5.5 \text{ V}, \text{ I}_{\text{OUT}} = 0 \text{ mA}, \text{ T}_{\text{A}} = 125 \text{ °C}$ | | | 0.60 | | μA | |
| | | V _{IN} =1.5 V, V _{EN} = 0 V, I _{OUT} | =0 mA | | 2 | 20 | |
| | | V_{IN} =1.5 V, V_{EN} = 0 V, I_{OUT} | =0 mA | | 3 | | nA |
| I _{SD} | Shut Down Current | V_{IN} =4.2 V, V_{EN} = 0 V, I_{OUT} | =0 mA | | 10 | |] IIA |
| ISD | Shut Down Current | V _{IN} =5.5 V, V _{EN} = 0 V, I _{OUT} =0 mA | | | 25 | 35 | |
| | | V_{IN} =5.5 V, V_{EN} = 0 V, I_{OUT} =0 mA, T_A =85 °C ⁽⁴⁾ | | | 0.30 | 0.45 | μA |
| | | V _{IN} =5.5 V, V _{EN} = 0 V, I _{OUT} =0 mA, T _A =125 °C | | | 2.30 | 3.00 | |
| | | V _{IN} =5.5 V, I _{OUT} = 500 mA | T _A =25 °C | | 60 | 68 | |
| | | | T _A = 125 °C | | 76 | | mΩ |
| | | V 2.2.V I 500 A | T _A =25 °C | | 70 | 79 | |
| | | V_{IN} =3.3 V, I_{OUT} = 500 mA | T _A = 125 °C | | 90 | | |
| Ron | On-Resistance | V -1 9 V I - 200 m A | T _A =25 °C | | 110 | 124 | |
| | | V _{IN} =1.8 V, I _{OUT} = 300 mA | T _A = 125 °C | | 132 | | |
| | | V _{IN} =1.5 V, I _{OUT} = 100 mA | T _A =25 °C | | 120 | 135 | |
| | | VIN-1.3 V, IOUT- IOUTIA | T _A = 125 °C | | 155 | | |

GLF1201Q

Nano Current Power I_QSmart[™] Switch with TRCB

| В | Output Discharge Begistenes | V _{EN} =Low, I _{FORCE} = 10 mA | | 85 | | |
|---|-------------------------------------|---|-----|-----|-----|------|
| R _{DSC} | Output Discharge Resistance | V _{EN} =Low, I _{FORCE} = 10 mA, T _A = 125 °C | | 90 | | Ω |
| W | CN Input Logic High Voltage | V _{IN} =1.5 V to 1.8 V, T _A = -40 °C to +125 °C | 1.1 | | | |
| V _{IH} | EN Input Logic High Voltage | V _{IN} =1.8 V to 5.5 V, T _A = -40 °C to +125 °C | | | | V |
| \/ | EN Input Logic Low Voltage | V _{IN} =1.5 V to 1.8 V, T _A = -40 °C to +125 °C | | | 0.3 |] |
| V _{IL} | EN Input Logic Low Voltage | V _{IN} =1.8 V to 5.5 V, T _A = -40 °C to +125 °C | | | 0.4 | |
| Ren | EN Internal Resistance | Internal Pull-down Resistance | | 10 | | ΜΩ |
| I _{EN} | EN Current | V _{EN} =5.5 V | | 0.5 | | μA |
| | RCB Protection Threshold | Vout - Vin | | 42 | | |
| V _{RCB_TH} | Voltage | V _{OUT} - V _{IN} , T _A = 125 °C | | 50 | | mV |
| V . | RCB Protection Release | V _{IN} - V _{OUT} | | 22 | |] "" |
| V _{RCB_RL} | Voltage | V _{IN} - V _{OUT} ,T _A = 125 °C | | 32 | |] |
| Switching | Characteristics (2), (3) | | | | | |
| t _{dON} | Turn-On Delay | B =150 0 C =0.1 uF | | 450 | | |
| t _R | V _{OUT} Rise Time | - R _L =150 Ω, C _{OUT} =0.1 μF | | 600 | |] |
| t _{dOFF} Turn-Off Delay ⁽⁴⁾ | | D -150 0 0 -0.1 uF | | 17 | | μs |
| t _F | V _{OUT} Fall Time (3), (4) | R _L =150 Ω, C _{OUT} =0.1 μF | | 12 | | |

Notes:

- IQ does not include the pull-down current of the enable pin through the REN.
- $t_{\rm ON}$ = $t_{\rm dON}$ + $t_{\rm R}$, $t_{\rm OFF}$ = $t_{\rm dOFF}$ + $t_{\rm F}$ Output discharge path is enabled when the device is enabled.
- Output discharge path is enabled when the second 4. By design; characterized, not production tested.

TIMING DIAGRAM

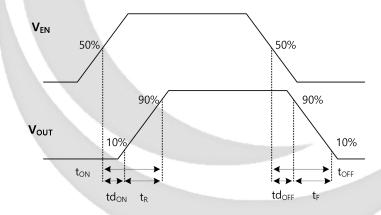
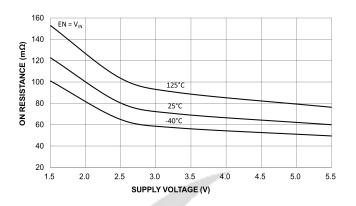


Figure 3. Timing Diagram



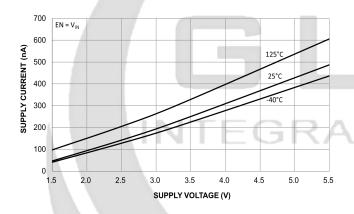
TYPICAL PERFORMANCE CHARACTERISTICS



160 FN = V.. 140 V_{IN}=1.5\ ON RESISTANCE (mΩ) 120 100 /_{IN}=2.5\ 80 60 40 20 -40 -25 125 $T_{\rm J}$, JUNCTION TEMPERATURE (°C)

Figure 4. On-Resistance vs. Supply Voltage

Figure 5. On-Resistance vs. Temperature



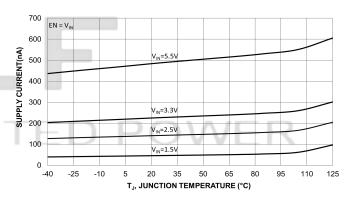
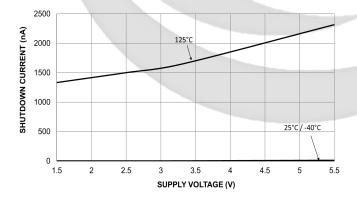


Figure 6. Quiescent Current vs. Supply Voltage

Figure 7. Quiescent Current vs. Temperature



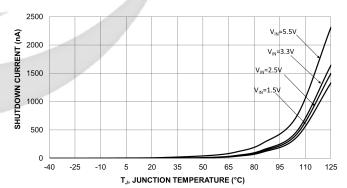
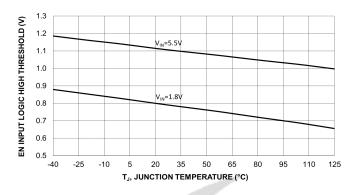


Figure 8. Shutdown Current vs. Supply Voltage

Figure 9. Shutdown Current vs. Temperature



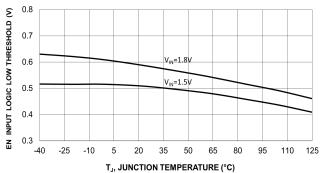
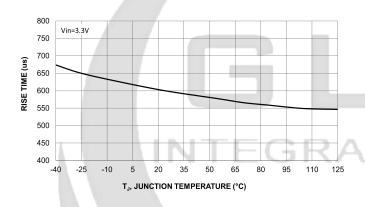


Figure 10. EN Input Logic High Threshold Vs. Temperature

Figure 11. EN Input Logic Low Threshold Vs. Temperature



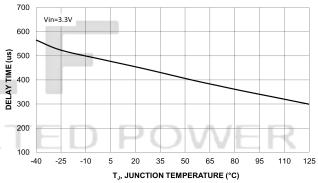


Figure 12. V_{OUT} Rise Time vs. Temperature

V_{EN} [2V/div]

Vout [1V/div] 400 us/div

Figure 13. Turn-On Delay Time vs. Temperature

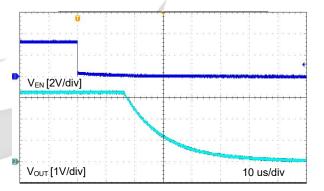


Figure 14. Turn-On Response $V_{\text{IN}}{=}3.3~\text{V},~C_{\text{IN}}{=}C_{\text{OUT}}{=}0.1~\mu\text{F},~R_{\text{L}}{=}150~\Omega$

Figure 15. Turn-Off Response $V_{IN}{=}3.3~V,~C_{IN}{=}C_{OUT}{=}0.1~\mu F,~R_L{=}150~\Omega$

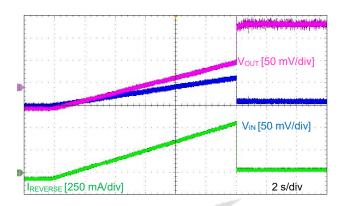


Figure 16. Reverse Current Blocking Threshold V_{IN} =3.3 V, V_{OUT} =Up to 3.4 V, C_{IN} = C_{OUT} =0.1 μ F, R_{L} =150 Ω

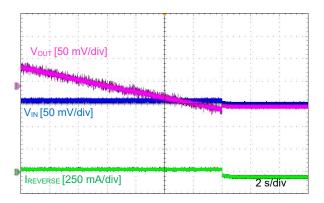


Figure 17. Reverse Current Blocking Release $V_{IN}=3.3~V,~V_{OUT}=Down~to~3.2~V,~C_{IN}=C_{OUT}=0.1~\mu F,~R_L=150~\Omega$

APPLICATION INFORMATION

The GLF1201Q integrated 2 A, ultra-efficient I_QSmart[™] load switch devices with a fixed slew rate control to limit the inrush current during turn on. It is capable of operating over a wide input range from 1.5 V to 5.5 V with low on-resistance to reduce conduction loss. In the off state, it consumes very low leakage current to lengthen the lifespan of a battery.

Input Capacitor

The GLF1201Q does not require an input capacitor. However, to reduce the voltage drop on the input power rail caused by transient inrush current at start-up, a 0.1 μ F capacitor is recommended to be placed close to the V_{IN} pin. A higher input capacitor value can be used to further attenuate the input voltage drop.

Output Capacitor

The GLF1201Q does not require an output capacitor. However, use of an output capacitor is recommended to mitigate voltage undershoot on the output pin when the switch is turning off. Undershoot can be caused by parasitic inductance from board traces or intentional load inductances. If load inductances do exist, use of an output capacitor can improve output voltage stability and system reliability. The Cout capacitor should be spaced close to the VOUT and GND pins.

EN pin

The GLF1201Q can be activated by forcing EN pin high level. Note that the EN pin has an internal pull-down resistor to help pull the main switch to a known "off state" when no EN signal is applied from an external controller.

True Reverse Current Blocking

The GLF1201Q has a built-in true reverse current blocking protection (TRCB) which always monitors the output voltage level regardless of the status of EN pin to check if it is greater than the input voltage. When the output voltage goes beyond the input voltage by 42 mV, the TRCB turns off the device immediately. Note that some reverse current can occur until the V_{RCB} is triggered. The main switch will resume normal operation when the output voltage drops below the input source by the TRCB protection release voltage.

Output Discharge Function

The GLF1201Q has an internal discharge NFET switch on the VOUT pin. When an EN signal turns off the main power switch, the NFET switch turns on to discharge an output capacitor quickly.

Thermal Consideration

The maximum power dissipation (PD(MAX)) depends on specific temperature conditions such as ambient temperature, a silicon junction temperature, printed circuit board conditions, and a thermal resistance of an IC. It can be calculated by the following equation The maximum junction temperature of the GLF1201Q is not allowed to exceed the maximum rating, 150 °C to insure normal functionality.

The continuous output current given in Figure 18 shows current capability at the ambient temperature, T_A. It is limited by the maximum junction temperature, the thermal resistance, and the rise of the Ron at the ambient temperature condition.

$$P_{D(max)} = \frac{T_{J(max)} - T_{A}}{\theta_{IA}}$$

ndition.
$$P_{D(max)} = \frac{T_{J(max)} - T_A}{\theta_{JA}}$$

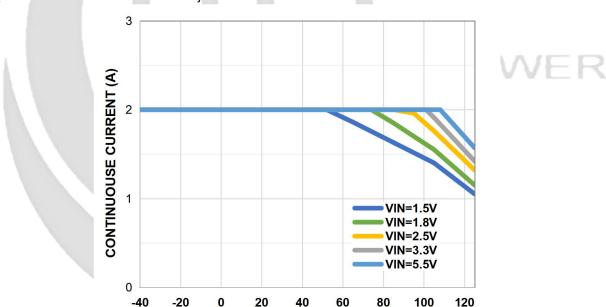
$$I_{D(DC)} = \sqrt{\frac{T_{J(max)} - T_A}{R_{DS} \cdot \theta_{JA}}}$$

Where

T_{J(max)}: Maximum junction temperature

: Ambient temperature

: Thermal resistance between junction and ambient



Note. This graph is based on a high effective thermal conductivity four-layer test board per JEDEC 51-7.

Figure 18. Continuous Current vs. Ambient Temperature

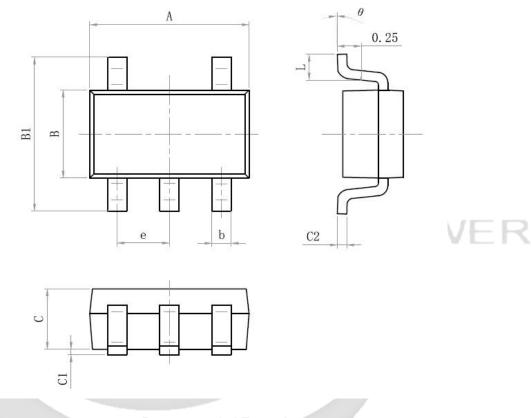
Board Layout

All traces should be as short as possible to minimize parasitic inductance effects. Wide traces for VIN, VOUT, and GND will help reduce signal degradation and parasitic effects during dynamic operation as well as improve the thermal performance at high load current.

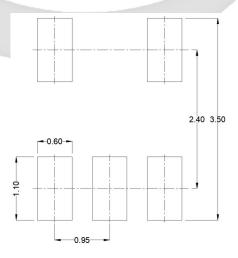


PACKAGE OUTLINE

| Size Mark | Min(mm) | Max(mm) | Size Mark | Min(mm) | Max(mm) |
|--------------|---------|----------|--------------|---------|---------|
| A | 2.82 | 3.02 | С | 1.05 | 1.15 |
| е | 0.9 | 95 (BSC) | C1 | 0.03 | 0.15 |
| b | 0.28 | 0.45 | C2 | 0.12 | 0.23 |
| В | 1.50 | 1.70 | L | 0.35 | 0.55 |
| B1 | 2.60 | 3.00 | θ | 0° | 8° |



Recommended Footprint

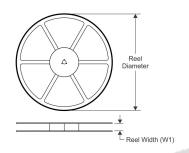


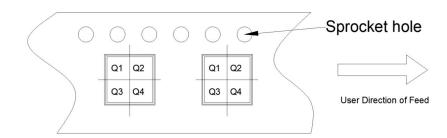


TAPE AND REEL INFORMATION

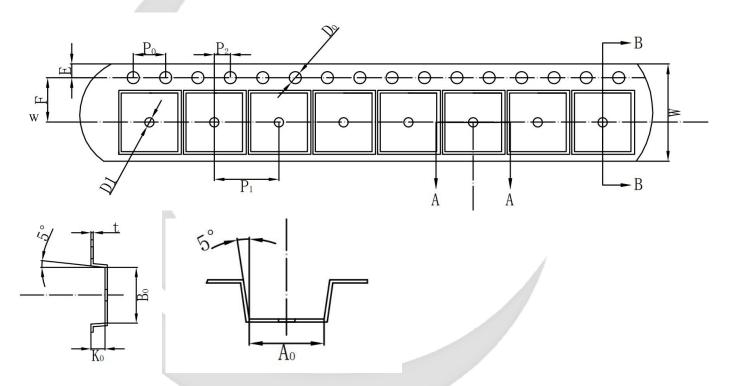
REEL DIMENSIONS

QUADRANT ASSIGNMENTS PIN 1 ORIENTATION TAPE





TAPE DIMENSIONS



| Device | Package | Pins | SPQ | Reel Diameter (mm) | Reel Width W1 | A0 | В0 | K0 | P1 | w | Pin1 |
|---------------|---------|------|------|-----------------------|------------------|------|------|------|----|---|------|
| GLF1201Q-T1G7 | SOT23-5 | 5 | 3000 | 178 | 9 | 3.25 | 3.30 | 1.38 | 4 | 8 | Q3 |

Remark:

- A0: Dimension designed to accommodate the component width
- B0: Dimension designed to accommodate the component length
- C0: Dimension designed to accommodate the component thickness
- W: Overall width of the carrier tape
- P1: Pitch between successive cavity centers

GLF1201Q

SPECIFICATION DEFINITIONS

| Document Type | Meaning | Product Status | | | |
|------------------------------|--|----------------|--|--|--|
| Target Specification | | | | | |
| Preliminary Specification | | | | | |
| Product Specification | This document represents the anticipated production performance characteristics of the device. | Production | | | |

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